



Docket No.: M4065.0369/P369  
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:  
Shane J. Trapp

Application No.: 09/752,685

Group Art Unit: 2813

Filed: January 3, 2001

Examiner: Thanhha-S. Pham

For: METHOD AND COMPOSITION FOR  
PLASMA ETCHING OF A SELF-ALIGNED  
CONTACT OPENING

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AMENDMENT UNDER 37 CFR § 1.116

ATTN: Box AF  
Commissioner for Patents  
Washington, DC 20231

Dear Sir:

This paper is responsive to the Office Action dated June 7, 2002, finally rejecting claims 1-25, 36-46, and 64-70. Please amend the above-captioned U.S. Patent application as follows.

IN THE CLAIMS:

Please replace claims with 1, 13, 14, 36, 43, and 64 with amended claims 1, 13, 14, 36, 43, and 64 below.

*Sub C17*

*B1*  
1. (twice amended) A method of forming an opening in an insulative layer formed over a substrate in a semiconductor device, comprising:

etching said insulative layer with an etching composition consisting essentially of ammonia and at least one fluorocarbon so as to form said opening, wherein the flow rate ratio of said at least one fluorocarbon to said ammonia is from about 2:1 to about 40:1.